



DMN2040U

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
001/	$25m\Omega @ V_{GS} = 4.5V$	6.0A
20V	$33m\Omega @ V_{GS} = 2.5V$	5.2A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- **Power Management Functions**

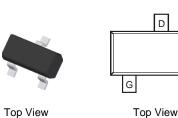
N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

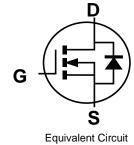
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



Top View

SOT23



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2040U-7	SOT23	3000/Tape & Reel
DMN2040U-13	SOT23	10000/Tape & Reel

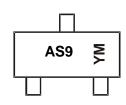
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. Notes:

2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



AS9 = Product Type Marking Code YM or \overline{YM} = Date Code Marking Y or \overline{Y} = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Kev

Date Obde Re	,											
Year	2017	2018	20	019	2020	2021		2022	2023	202	24	2025
Code	E	F		G	Н	I		J	K	L		М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	20	V		
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$ Steady State $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		ID	6.0 4.8	A	
Maximum Continuous Body Diode Forward Curre	IS	1.6	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	I _{DM}	30	А		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	159	°C/W
Total Power Dissipation (Note 6)		PD	1.36	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _θ JA	92	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						•
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	—	1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	—	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note7)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	—	1.2	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	D		21	25		$V_{GS} = 4.5V, I_D = 8.2A$
Static Drain-Source On-Resistance	R _{DS(ON)}	—	26	33	mΩ	$V_{GS} = 2.5V, I_D = 3.3A$
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	_	667	_	pF	
Output Capacitance	C _{oss}	_	91	—	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	83	—	pF	1 - 1.00012
Gate Resistance	R _g	_	1.2	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Qg	_	7.5	_	nC	
Gate-Source Charge	Q _{gs}	_	0.8	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Drain Charge	Q _{gd}	_	2.5	—	nC	$I_D = 8.2A$
Turn-On Delay Time	t _{D(ON)}	_	3.9	_	ns	
Turn-On Rise Time	t _R	_	5.1	—	ns	V _{DD} = 10V, V _{GS} = 4.5V,
Turn-Off Delay Time	t _{D(OFF)}	_	21	—	ns	$R_L = 10\Omega, R_g = 6\Omega$
Turn-Off Fall Time	tF	_	9.4	—	ns	1
Reverse Recovery Time	t _{RR}	_	12	_	ns	I _F = 5.0A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	_	3.4	_	nC	I _F = 5.0A, di/dt = 100A/µs

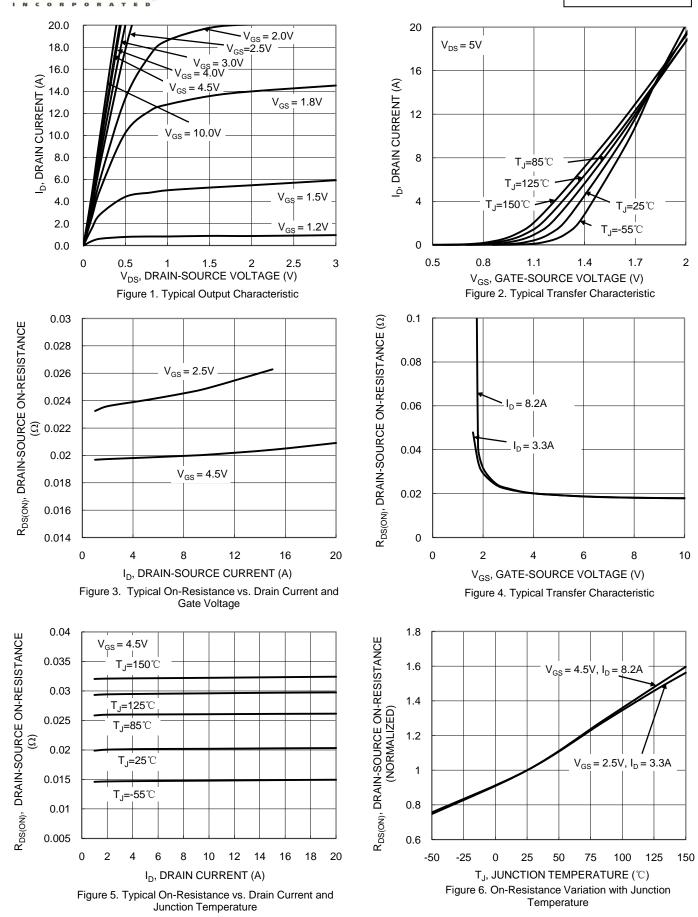
 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

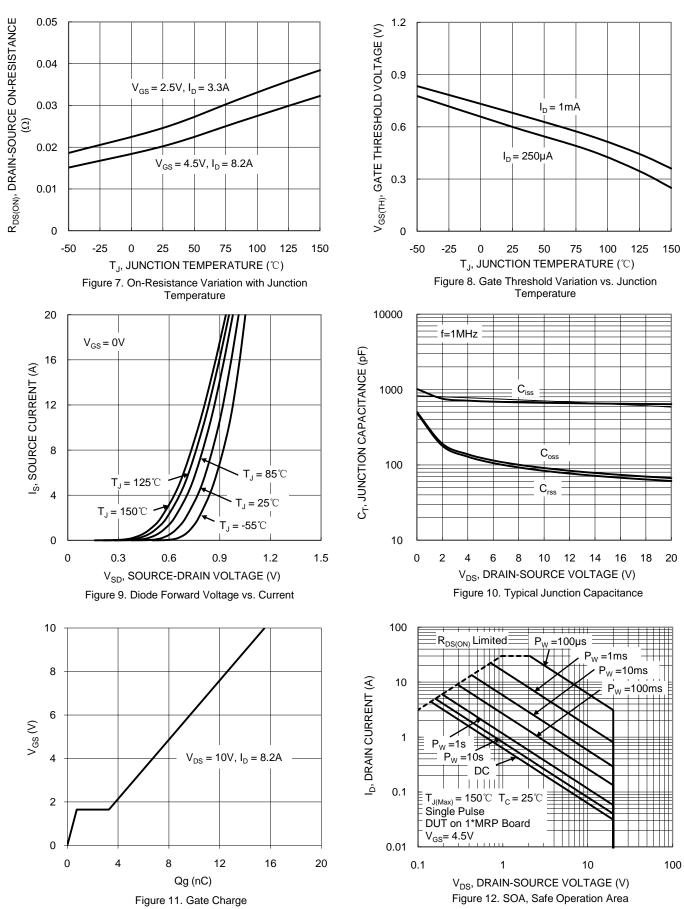


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DMN2040U Document number: DS40476 Rev. 3 - 2



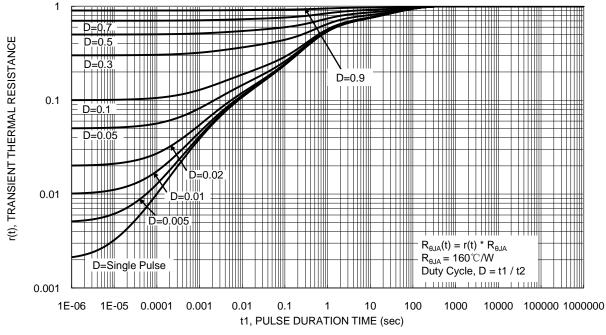
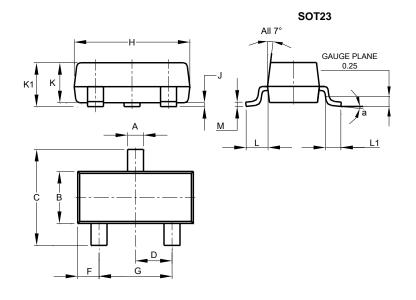


Figure 13. Transient Thermal Resistance



Package Outline Dimensions

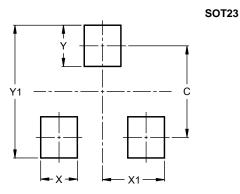
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
К	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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